IN THE SPECIFICATION

Page 4, in the "Brief Description of the Drawings" section, please amend as follow.

Figure 1 is a cross-sectional view of a semiconductor structure according to one embodiment of the present invention.

Figure 1A is a cross-sectional view of a semiconductor structure according to another embodiment of the present invention.

Figure 2 is an elevation view of a semiconductor memory array according to one embodiment of the present invention.

Page 8, the paragraph beginning on line 10, please amend as follow.

The inhibiting layer 130 acts to inhibit such compromise from occurring. In one embodiment, the inhibiting layer 130 acts to enhance the conductivity between the metallization layer 140 and the capacitor 136. In another embodiment, the inhibiting layer 130 acts to inhibit formation of an undesired dielectric between the metallization layer 140 and the electrode 128. In another embodiment, the inhibiting layer 130 acts to inhibit a diffusion that increases resistivity between the metallization layer 140 and the electrode 128. In another embodiment, the inhibiting layer 130 acts to inhibit formation of an undesired oxidation compound so as to enhance an ohmic contact between the metallization layer 140 and the electrode 128. The term "ohmic contact" means the inclusion of a metal-metal contact, metal-semiconductor contact, or semiconductor-semiconductor contact that has an approximately linear current-voltage characteristic. In another embodiment, the inhibiting layer 130 includes a layer that is disposed on the electrode 128. In another embodiment, the inhibiting layer 130 includes a layer that is embedded in the electrode 128 (as shown in FIG. 1A). In one embodiment, the inhibiting layer comprises a substance selected from a group consisting of a transition metal, a transition metal alloy, a nitride compound, a noble metal, and a noble metal alloy. In one embodiment, the transition metal is selected from a group consisting of platinum, rhodium, and tungsten. In another embodiment, the transition metal alloy includes a platinum rhodium alloy. In another embodiment, the nitride compound is selected from a group consisting of tungsten nitride and titanium nitride. In a further embodiment, the noble metal includes platinum, gold, titanium, and silver. In yet another

embodiment, the noble metal alloy includes graphite, chlorimet 3, and hastelloy C. Although the aforementioned embodiments focus on the electrode 128, electrode 124 may be used instead if the metallization layer 140 is adapted to contact the electrode 124.